SCHOOL OF ELECTRONICS ENGINEERING

KALINGA INSTITUTE OF INDUSTRIAL TECHNOLOGY (KIIT)



VLSI LABORATORY REPORT (EC-3095)

Submitted By

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Section: ETC-06

Semester: 6th semester

Experiment: 4th

Design of 1Kx8 RAM cell and its READ, WRITE operation.

Experiment No-04

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Aim of the Experiment: Design a I K × 8 R AM using behavioral modelling.

Software used:

EDA flay ground

In computing, memory enefers to a device that is used to store information. For immediate use in a computer or nelated to semiconductor memory. It is typically reffered to as semiconductor memory, specially MOS memory, where data is stored within Mosmemory cells on a silicon integrated circuit chip. Host semiconductor memory is organized into memory all or histable flip-flops, each storing one list.

Random access memory (RAM) is a form of computer memory that can be need and changed in any order, typically used to store working data and machine code.

A random access memory device allows data items to be read or written in almost the same amount of time irrespective of the physical location of Data inside the memory.

Design I-KB RAM

data time = 8 luits Memory space = 8 × 1.02 \$4 address lines = 10 luits.

1233 19 9 9 2x 2 1 0 1 15

Codes:-

Design.sv

```
// Code your design here
module ram(output [7:0]dout, input [7:0]din, input [9:0]addr, input clk,en,rw);
 reg [7:0]dout;
 reg [7:0]raw[1023:0];
 always@(negedge clk) begin
  if(en == 1'b1) begin
   if(rw == 1'b1) begin
    raw[addr] = din;
       dout \le 8'bx;
   end
   else
    dout <= raw[addr];</pre>
   end
  else
   dout \le 8'bz;
 end
endmodule
Testbench.sv
// Code your testbench here
// or browse Examples
module ram_tb;
 reg en,rw,clk;
 reg [7:0]din;
 reg [9:0]addr;
 wire [7:0]dout;
 ram r1(dout,din,addr,clk,en,rw);
 initial begin
  $dumpfile("dump.vcd"); $dumpvars;
  clk=0;en=1;rw=1;
  addr=8'ha;din=8'h14;#20;
  addr=8'hff;din=8'h32;#20;
  rw=0;
  addr=8'ha;#20;
  addr=8'hff;#20;
  addr=8'h5;#20;
  en=0;#20;
 end
 always #5 clk=!clk;
endmodule
```

Observations



Fig 4.1: EPWAVE diagram of 8kB RAM

Debagnik Kaz 1804373 Conclusion: In this experiment we learned about computer memory, and specially about RAM. EDA play ground by wer writing a code and one also simulated outfut manuform of IKBRAM by writing testhench code in EDA play ground.